2SD0814A (2SD814A)

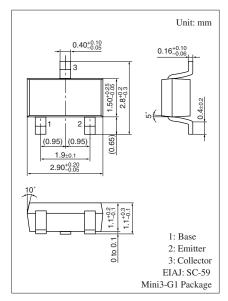
Silicon NPN epitaxial planar type

For high breakdown voltage low-frequency and low-noise amplification

Features

- \bullet High collector-emitter voltage (Base open) $V_{\mbox{\scriptsize CEO}}$
- Low noise voltage NV
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings $T_a = 25^{\circ}C$ Parameter Symbol Rating Unit V_{CBO} V Collector-base voltage (Emitter open) 185 Collector-emitter voltage (Base open) V_{CEO} 185 V 5 V Emitter-base voltage (Collector open) V_{EBO} 50 Collector current I_C mА Peak collector current 100 mA I_{CP} $P_{\rm C}$ Collector power dissipation 200 mW °C Junction temperature Ti 150 °C Storage temperature T_{stg} -55 to +150



Marking Symbol: L

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|-----|-----|-----|------|
| Collector-emitter voltage (Base open) | V _{CEO} | $I_{C} = 100 \ \mu A, I_{B} = 0$ | | | | V |
| Emitter-base voltage (Collector open) | V _{EBO} | $I_E = 10 \ \mu A, \ I_C = 0$ | 5 | | | V |
| Collector-base cutoff current (Emitter open) | I _{CBO} | $V_{CB} = 100 \text{ V}, I_E = 0$ | | | 1 | μΑ |
| Forward current transfer ratio * | h _{FE} | $V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$ | 90 | | 330 | _ |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_{\rm C} = 30 \text{ mA}, I_{\rm B} = 3 \text{ mA}$ | | | 1 | V |
| Transition frequency | f _T | $V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |
| Collector output capacitance | C _{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 2.3 | | pF |
| (Common base, input open circuited) | | | | | | |
| Noise voltage | NV | $V_{CE} = 10 \text{ V}, I_C = 1 \text{ mA}, G_V = 80 \text{ dB}$ | | 150 | | mV |
| | | $R_g = 100 \text{ k}\Omega$, Function = FLAT | | | | |

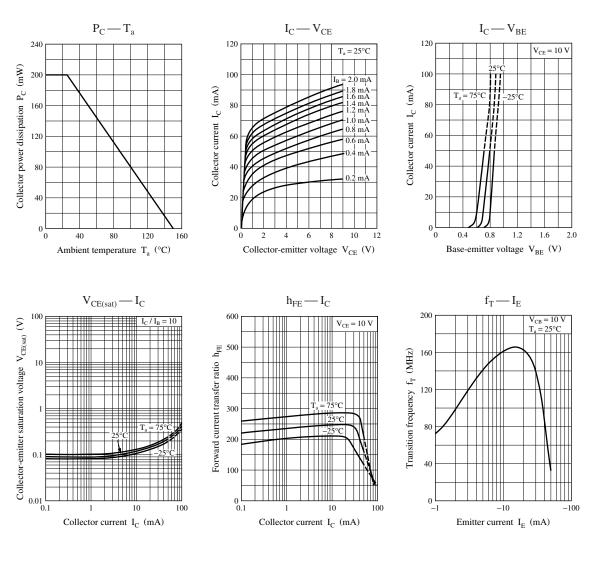
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

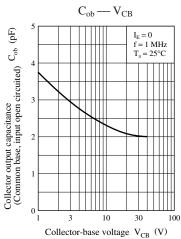
2. *: Rank classification

| Rank | Q | R | S | |
|--------------|-----------|------------|------------|--|
| $h_{\rm FE}$ | 90 to 155 | 130 to 220 | 185 to 330 | |

Note) The part number in the parenthesis shows conventional part number.

Panasonic





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